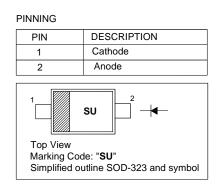
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Features

- Low forward voltage
- Low reverse current

Applications

• High Speed Switching



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V _{RM}	45	V
Reverse Voltage	V _R	40	V
Average Forward Current	Ι _ο	100	mA
Maximum (Peak) Forward Current	I _{FM}	300	mA
Surge Forward Current (10 ms)	I _{FSM}	1	А
Power Dissipation	P _{tot}	150	mW
Junction Temperature	TJ	125	°C
Operating Temperature Range	T _{opr}	- 40 to + 100	°C
Storage Temperature Range	T _s	- 55 to + 125	°C

Characteristics at T_a = 25 °C

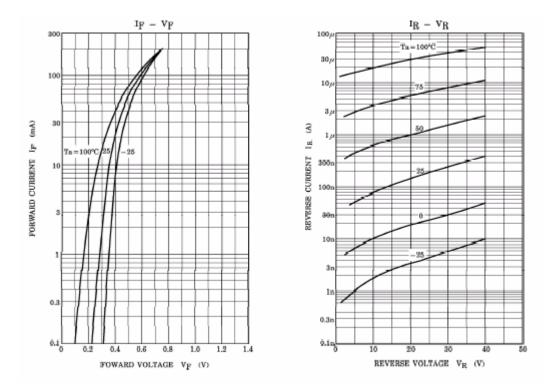
Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	0.6	V
Reverse Current at $V_R = 40 V$	I _R	5	μA
Total Capacitance at f = 1 MHz	C _T	25	pF

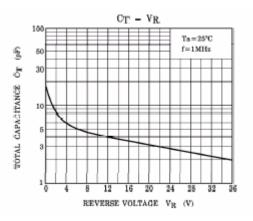






Dated : 01/09/2006









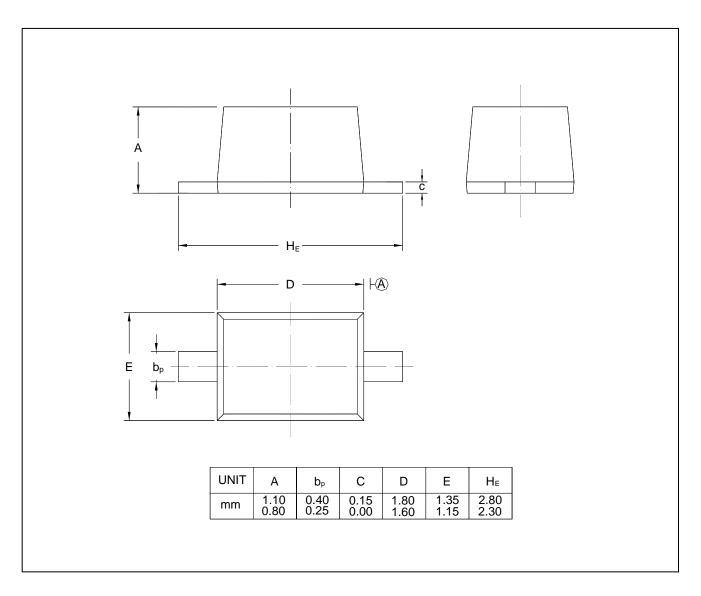


Dated : 01/09/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323









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